

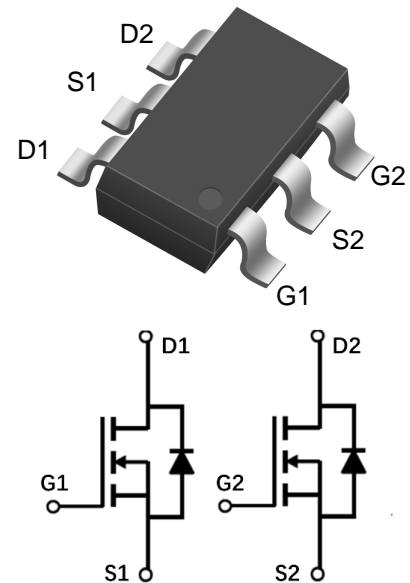
Description:

This Dual N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=30V, I_D=6A, R_{DS(ON)}<23m\ \Omega @V_{GS}=10V$ (Typ: $18m\ \Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOC3400B	3400B	SOT-23-6D	3000pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_A=25^\circ\text{C}^1$	6	A
	Continuous Drain Current- $T_A=100^\circ\text{C}^1$	4.2	
I_{DM}	Pulsed Drain Current ²	24	
P_D	Power Dissipation	1.3	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	95	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu A$	30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=30V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0A$	---	---	± 10	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu A$	0.6	0.84	1.5	V
$R_{DS(on)}$	Drain-Source On Resistance ³	$V_{GS}=10V, I_D=4.2A$	---	18	23	$m\ \Omega$
		$V_{GS}=4.5V, I_D=4A$	---	20	26	$m\ \Omega$
		$V_{GS}=2.5V, I_D=1A$	---	27	40	$m\ \Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	820	---	pF
C_{oss}	Output Capacitance		---	68	---	
C_{rss}	Reverse Transfer Capacitance		---	56.7	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=15V, I_D=3A$ $R_{ENG}=3\ \Omega, V_{GS}=10V$	---	4	---	ns
t_r	Rise Time		---	11.5	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	25	---	ns
t_f	Fall Time		---	2	---	ns
Q_g	Total Gate Charge	$V_{GS}=4.5V, V_{DS}=15V,$ $I_D=3A$	---	9.5	---	nC
Q_{gs}	Gate-Source Charge		---	2	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	2.1	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=5.8A$	---	---	1.2	V
I_S	Continuous Drain Current	$V_D=V_G=0V$	---	---	5	A
I_{SM}	Pulsed Drain Current		---	---	20	A
T_{rr}	Reverse Recovery Time	$I_F=3A, T_J=25^{\circ}\text{C}$	---	8.4	---	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	---	3.3	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_A=25^\circ C$ unless otherwise noted)

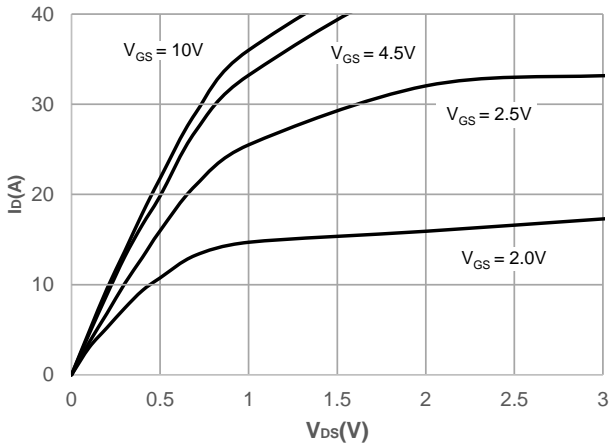


Figure 1: Output Characteristics

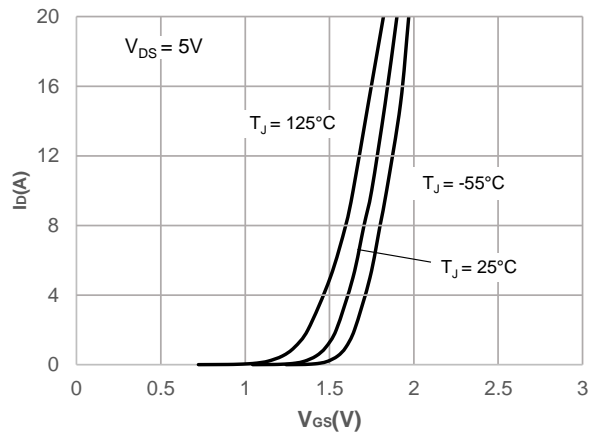


Figure 2: Typical Transfer Characteristics

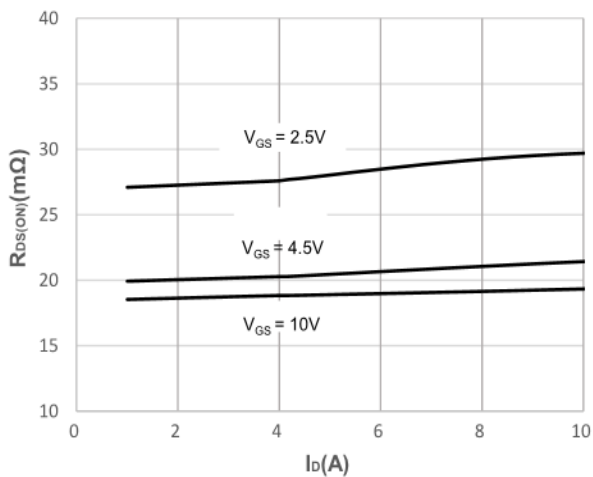


Figure 3: On-resistance vs. Drain Current

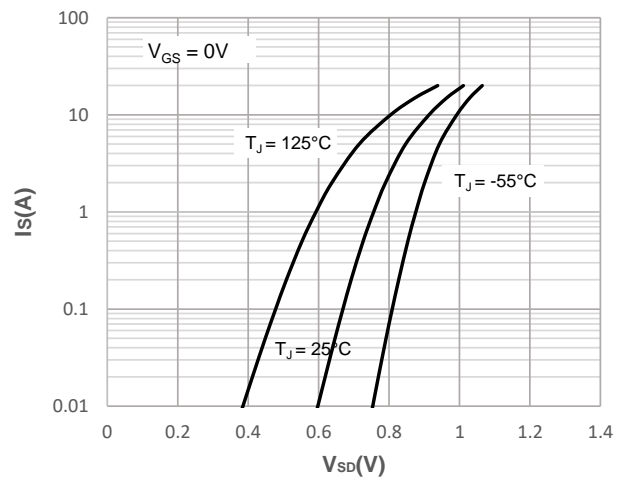


Figure 4: Body Diode Characteristics

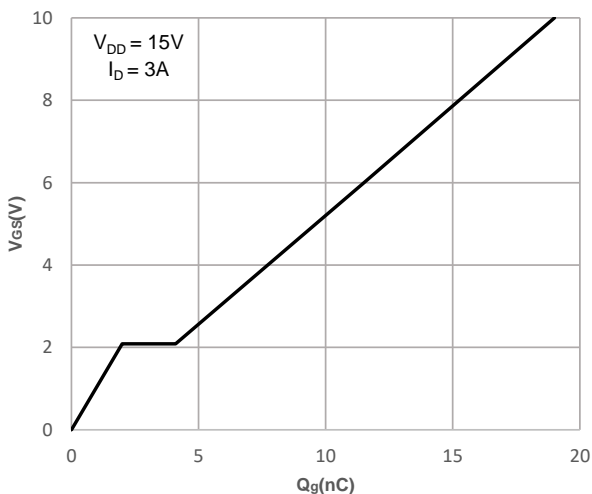


Figure 5: Gate Charge Characteristics

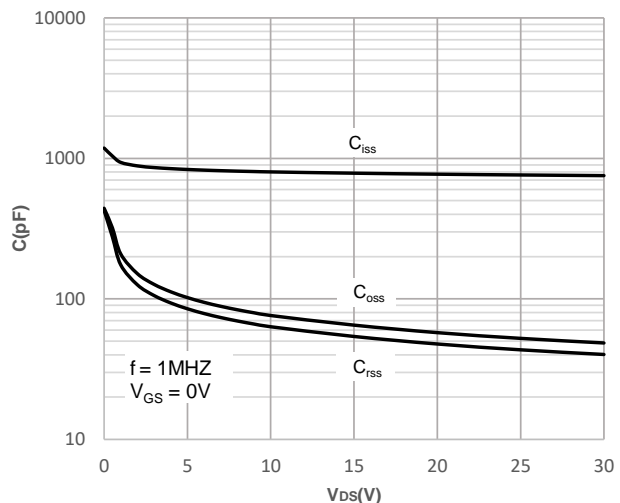


Figure 6: Capacitance Characteristics

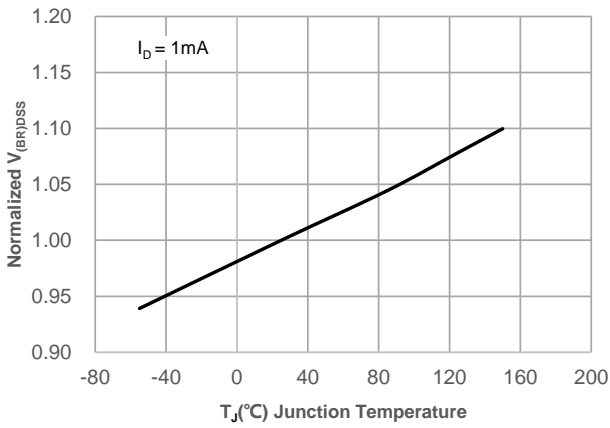


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

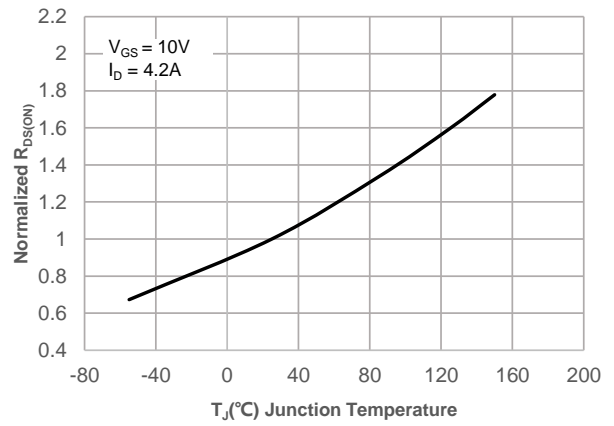


Figure 8: Normalized on Resistance vs. Junction Temperature

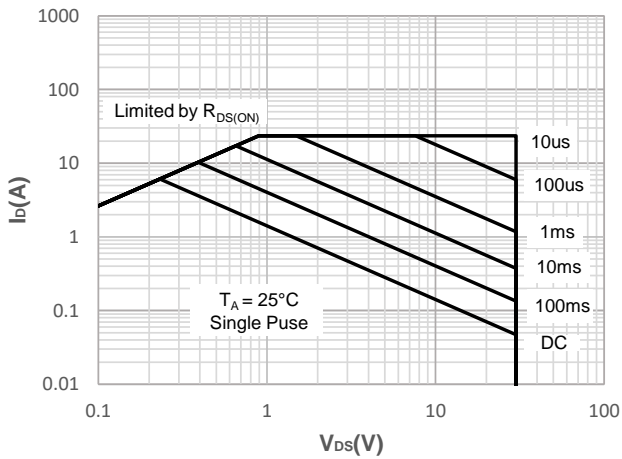


Figure 9: Maximum Safe Operating Area

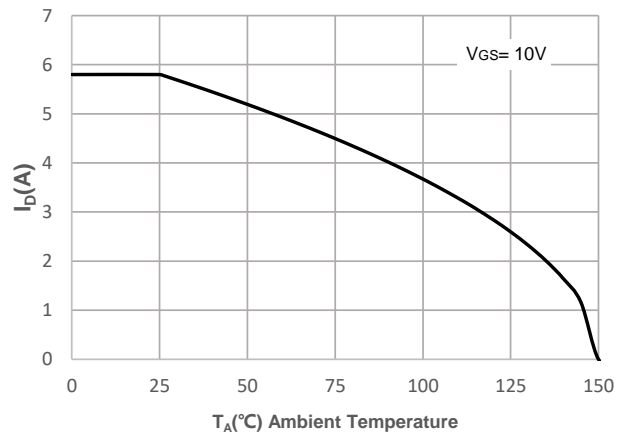


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

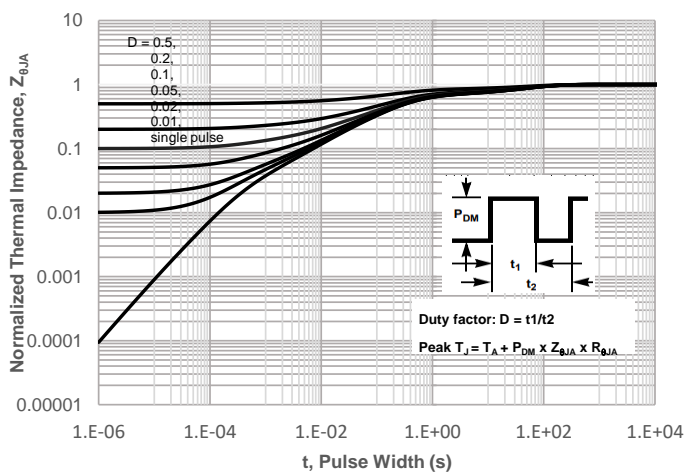


Figure 11: Normalized Maximum Transient Thermal Impedance

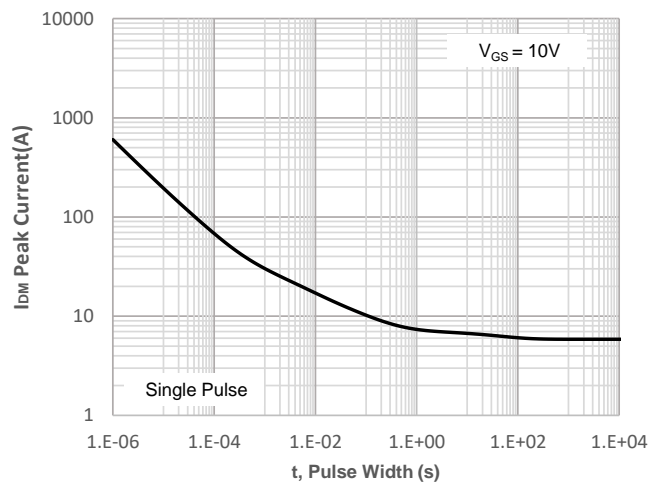
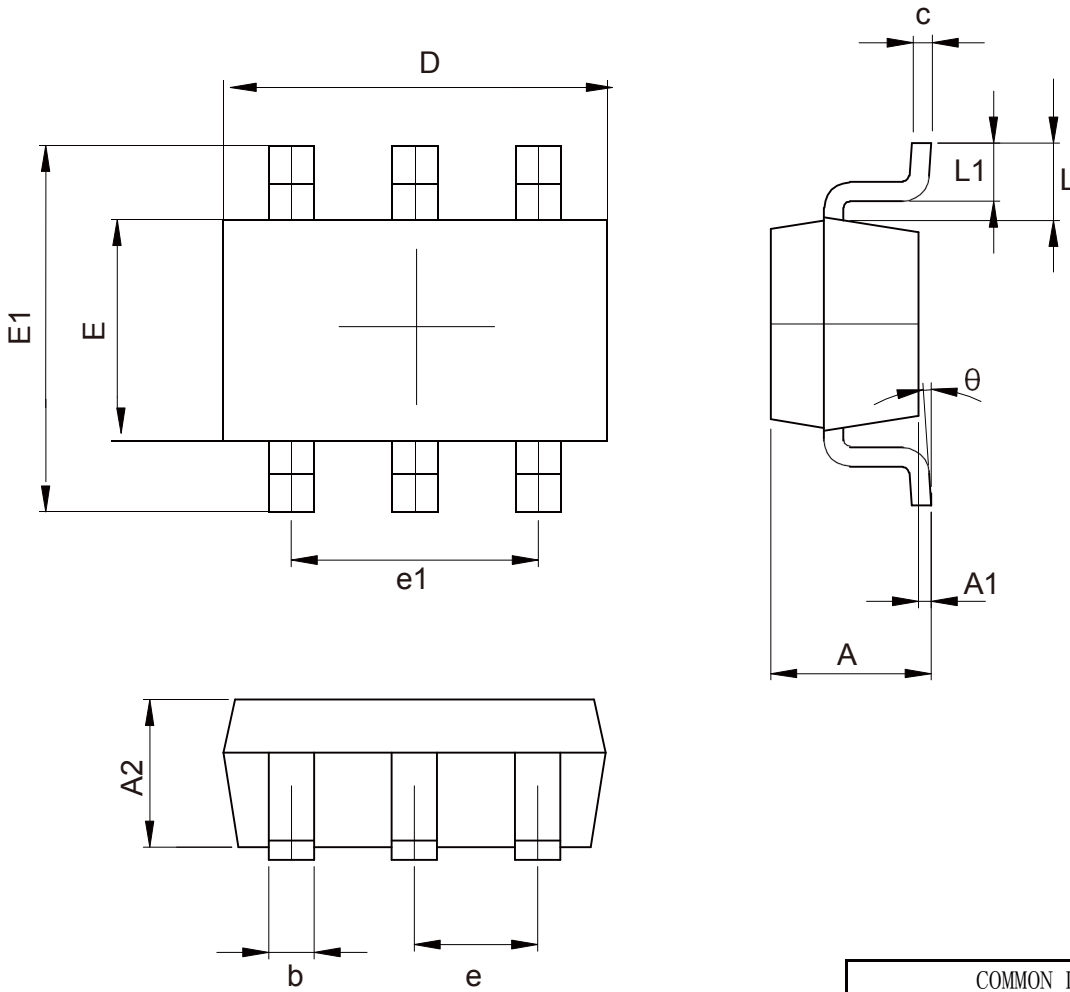


Figure 12: Peak Current Capacity

SOT-23-6D Package Outline Data

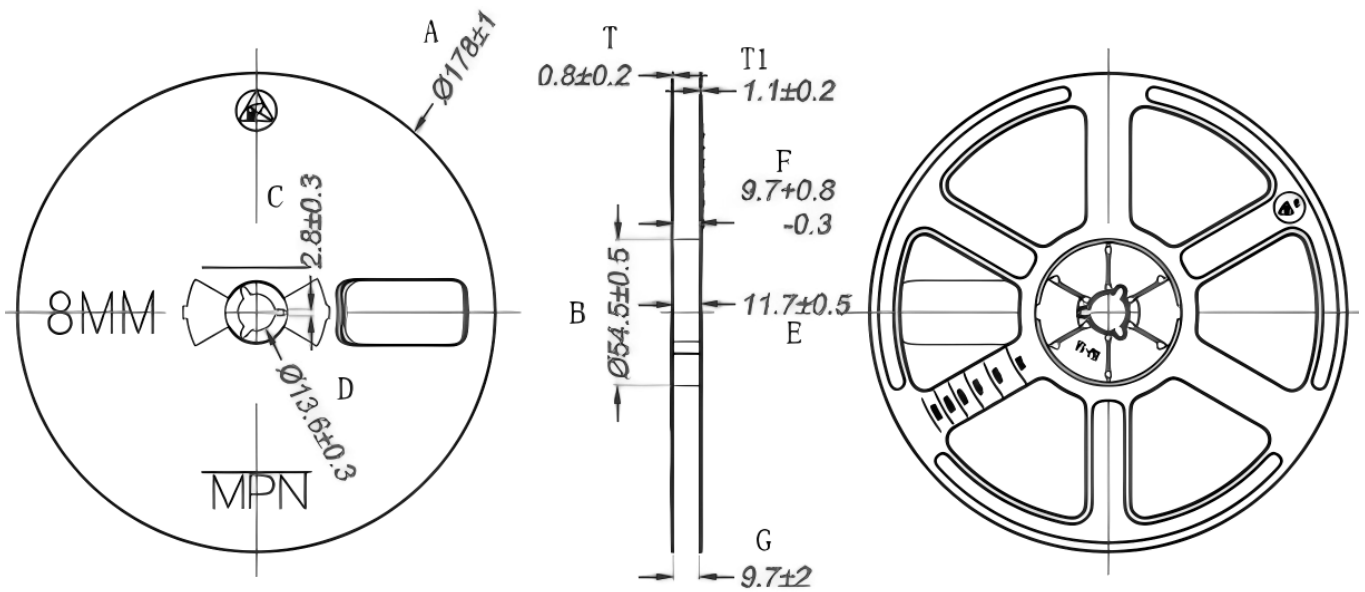


COMMON DIMENSIONS			
UNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	1.050	---	1.300
A1	0.000	---	0.200
A2	1.050	---	1.200
b	0.300	0.400	0.500
c	0.100	---	0.200
D	2.820	2.900	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.6REF		
L1	0.300	0.450	0.600
θ	0°	--	8°

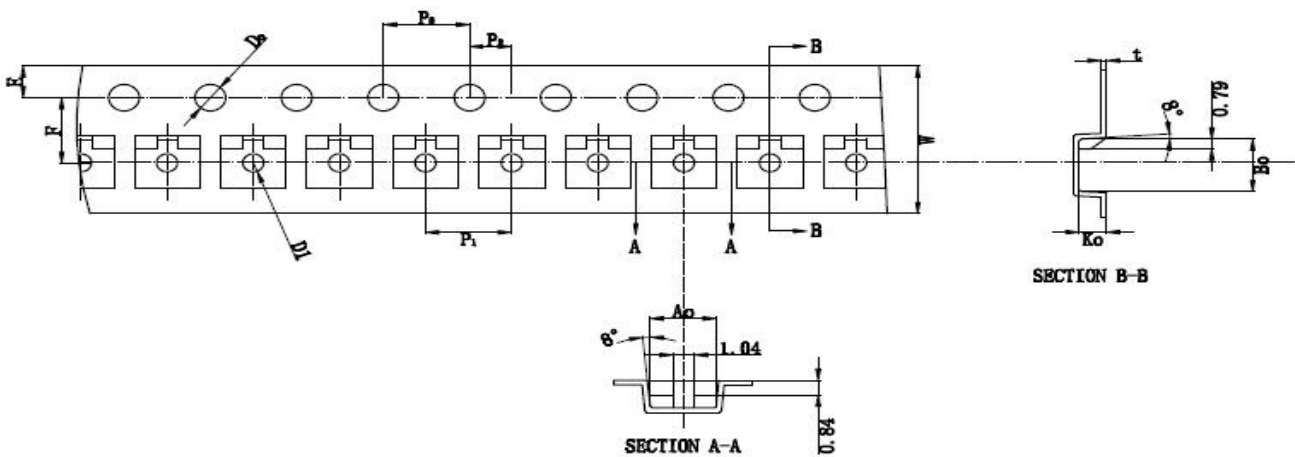
Unit:mm

Tape & Reel Information

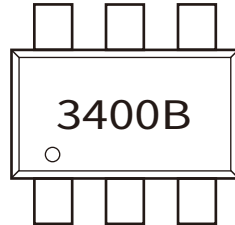
Dimensions in mm



PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2	A0	B0	K0	T
SOT23-6	8.00	4.00	1.75	3.50	1.50	1.00	4.00	40.00	2.00	3.13	3.22	1.30	0.20
Tolerance	±0.2	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.2	±0.1	±0.1	±0.1	±0.1	±0.03



Pulling direction →

Marking Information:**Previous Version**

Version	Date	Subjects (major changes since last revision)
1.0	2025-09-10	Release of final version

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